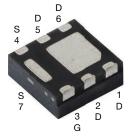
SQA409CEJW

www.vishay.com

Vishay Siliconix

Automotive P-Channel 12 V (D-S) 175 °C MOSFET





Top View Marking Code: QAAXXXX

Bottom View

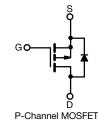
PRODUCT SUMMARY				
V _{DS} (V)	-12			
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	0.019			
$R_{DS(on)} (\Omega)$ at $V_{GS} = -2.5 V$	0.026			
$R_{DS(on)} (\Omega)$ at $V_{GS} = -1.8 V$	0.040			
I _D (A)	-9			
Configuration	Single			

PowerPAK[®] SC-70W-6L Single

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 gualified
- Wettable flank terminals
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ORDERING INFORMATIO	N
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Package	PowerPAK SC-70W-6L
Lead (Pb)-free and halogen-free	SQA409CEJW (for detailed order number please see <u>www.vishay.com/doc?79776</u>)

ABSOLUTE MAXIMUM RATINGS ($T_c = 25 \degree C$, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage Gate-source voltage		V _{DS}	-12	V		
		V _{GS}	± 8	V		
Continuous drain current ^a	T _C = 25 °C	I	-9			
	T _C = 125 °C	I _D	-9			
Continuous source current (diode conduction) a		I _S	-9	А		
Pulsed drain current ^b	sed drain current ^b		-36			
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-15			
Single pulse avalanche energy	L = 0.1 MH	E _{AS}	11.25	mJ		
Maximum power dissipation	T _C = 25 °C	D	13.6	W		
	T _C = 125 °C	P _D	4.5	vv		
Operating junction and storage temperature range Soldering recommendations (peak temperature) ^{d, e}		T _J , T _{stg}	-55 to +175	°C		
		-	260	C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount ^c	R _{thJA}	90	°C/W		
Junction-to-case (drain)		R _{thJF}	11	0/10		

Notes

a. Package limited

b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

c. When mounted on 1" square PCB (FR4 material)

See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70W-6L is a leadless package and features wettable flank terminals. The end of the lead terminal is plated with tin d.

- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components Not intended for continuous use with positive gate voltage > 3.0 V e. f.

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1 For technical questions, contact: automostechsupport@vishay.com Document Number: 62125

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SQA409CEJW

SPECIFICATIONS ($T_C = 25 \text{ °C}$, u	nless otherv	vise noted)				_		
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = -250 μA		-12	-	-	v	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = -250 µA	-0.45	-0.7	-1.0	v	
Gate-source leakage	I _{GSS}	V _{DS} =	= 0 V, V _{GS} = ± 8 V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = -12 V	-	-	-1		
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -12 V, T _J = 125 °C	-	-	-50	μA	
		$V_{GS} = 0 V$	V _{DS} = -12 V, T _J = 175 °C	-	-	-150		
On-state drain current ^a	I _{D(on)}	$V_{GS} = -4.5 V$	$V_{DS} \ge 5 V$	-8	-	-	Α	
Drain-source on-state resistance ^a		$V_{GS} = -4.5 V$	I _D = -4.5 A	-	0.0142	0.019		
		$V_{GS} = -4.5 V$	I _D = -4.5 A, T _J = 125 °C	-	-	0.0253	Ω	
	R _{DS(on)}	$V_{GS} = -4.5 V$	I _D = -4.5 A, T _J = 175 °C	-	-	0.0288		
		$V_{GS} = -2.5 V$	I _D = -3 A	-	0.0198	0.026		
		V _{GS} = -1.8 V	I _D = -2 A	-	0.0303	0.040		
Forward transconductance b	9 _{fs}	V _{DS} = -10 V, I _D = -4 A			20	-	S	
Dynamic ^b		-			-			
Input capacitance	C _{iss}		0 V V _{DS} = -6 V, f = 1 MHz	-	2191	3070	pF	
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	374	525		
Reverse transfer capacitance	C _{rss}			-	361	510		
Total gate charge ^c	Qg				22	33		
Gate-source charge ^c	Q _{gs}	$V_{GS} = -4.5 V$	$V_{DS} = -6 V, I_D = -8 A$	-	5	-	nC	
Gate-drain charge ^c	Q _{gd}			-	6	-		
Gate resistance	R _g	f = 1 MHz		3.2	6.45	9.7	Ω	
Turn-on delay time ^c	t _{d(on)}			-	15	25		
Rise time ^c	t _r		= -6 V, R _L = 2.4 Ω	-	33	50		
Turn-off delay time ^c	t _{d(off)}	$I_D \cong$ -2.5 Å, V_{GEN} = -4.5 V, R_g = 1 Ω		-	61	95	ns	
Fall time ^c	t _f				44	70		
Source-Drain Diode Ratings and Charac	teristics	- -			-			
Pulsed current ^a	I _{SM}			-	-	-36	А	
Forward voltage	V _{SD}	$I_F = -4.5 \text{ A}, V_{GS} = 0$		-	-0.72	-1.2	V	
Body diode reverse recovery time	t _{rr}			-	14	28	ns	
Body diode reverse recovery charge	Q _{rr}	I _F = -2 A, di/dt = 100 A/μs		-	6	12	nC	
Reverse recovery fall time	t _a			-	7	-	-	
Reverse recovery rise time	t _b			-	7	-	ns	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-0.8	-	А	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

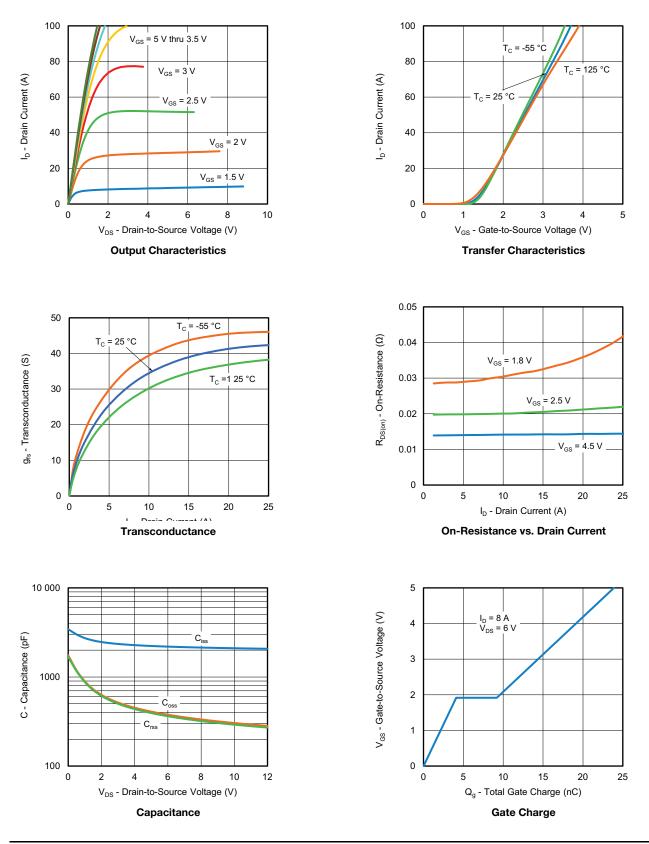
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



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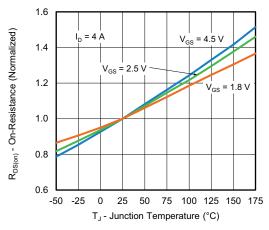
3

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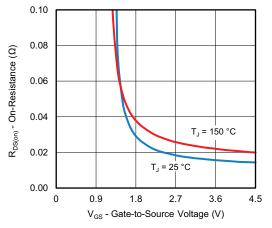


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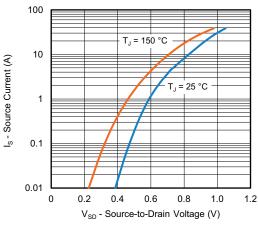
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



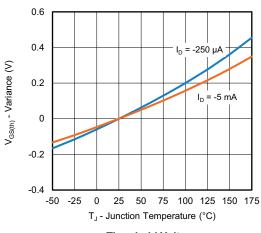
On-Resistance vs. Junction Temperature



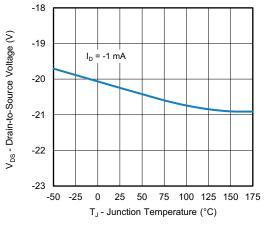
On-Resistance vs. Gate-to-Source Voltage



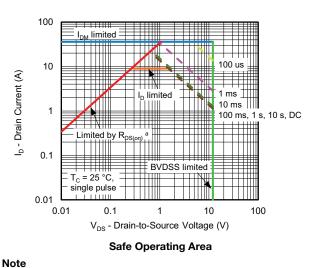
Source-Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

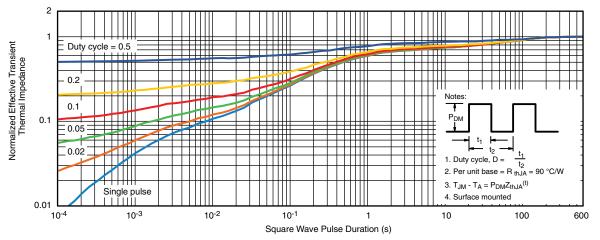
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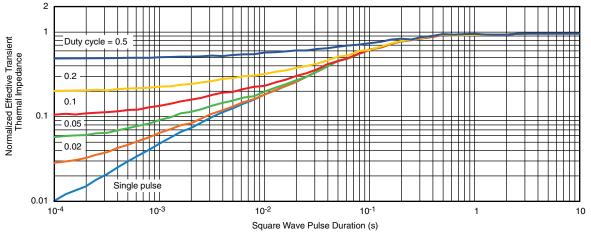


Vishay Siliconix

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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